

12V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
40)/	8mΩ @ V _{GS} = 4.5V	12.2A
12V	12.5mΩ @ $V_{GS} = 2.5V$	10.4A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Battery Management Application
- Power Management Functions
- DC-DC Converters

Features

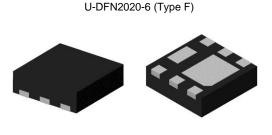
- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- · Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part.
 A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
 https://www.diodes.com/quality/product-definitions/

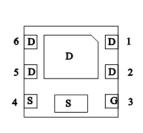
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0065 grams (Approximate)

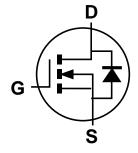




Bottom View



Pin Out Bottom View



Internal Schematic

Ordering Information (Note 4)

Part Number	Reel Size (inches)	Case	Quantity per Reel
DMN1008UFDF-7	7	U-DFN2020-6 (Type F)	3,000
DMN1008UFDF-13	13	U-DFN2020-6 (Type F)	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site 1



8N = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Date Code Ney												
Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	С		Н		J	K	L	М	N	0	Р	R
	-		l I		I			l I	l I	l I	I	
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



8N = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Code 5 0 1 2 3 4 5 6 7 8 9	Year	2015	 2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
	Code	5	 0	1	2	3	4	5	6	7	8	9

Week	1-26	27-52	53
Code	A-Z	a-z	z

Ī	Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Ī	Code	Т	U	V	W	X	Υ	Z



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V_{DSS}	12	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current, V _{GS} = 4.5V (Note 6)	I _D	12.2 9.8	А		
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%	6)		I _{DM}	60	Α
Continuous Source-Drain Diode Current (Note 6)	Is	1.8	Α		
Avalanche Current, L = 0.1mH (Note 7)	I _{AS}	16.4	Α		
Avalanche Energy, L = 0.1mH (Note 7)			E _{AS}	13.5	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Dawer Dissination (Note 5)	T _A = +25°C	-	0.7	W
Total Power Dissipation (Note 5)	T _A = +70°C	P_{D}	0.4	VV
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	168	°C/W
Total Davies Discipation (Note C)	T _A = +25°C	Б.	1.7	W
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	P_{D}	1.0	VV
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	74	°C/W
Thermal Resistance, Junction to Case (Note 6)	·	R _{0JC}	12	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

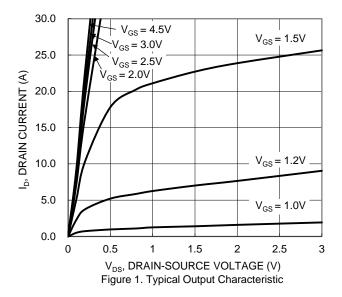
Electrical Characteristics ($@T_A = +25$ °C, unless otherwise specified.)

			•			
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	12		_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	1	1	μA	$V_{DS} = 9.6V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	0.3	-	1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
			6.6	8		$V_{GS} = 4.5V, I_D = 5A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	7.6	11	mΩ	$V_{GS} = 3.0V, I_D = 5A$
	, ,		8.5	12.5		$V_{GS} = 2.5V, I_D = 5A$
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	$V_{GS} = 0V$, $I_S = 5A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	_	995	_		., ., ., .,
Output Capacitance	Coss	_	305	_	pF	$V_{DS} = 6V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	270	_		I = 1.0IVIHZ
Gate Resistance	R_g	_	1.5	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = 4.5V)	Q_g	_	13.6	_		
Total Gate Charge (V _{GS} = 8V)	Q_g	_	23.4	_	nC	$V_{DS} = 6V, I_{D} = 5A$
Gate-Source Charge	Q_{gs}	_	1.3	_	IIC	$V_{DS} = 6V$, $I_D = 5A$
Gate-Drain Charge	Q_{gd}	_	3.3	_		
Turn-On Delay Time	t _{D(ON)}	_	3.5	_		
Turn-On Rise Time	t _R	_	6.6	_	ns	$V_{DS} = 6V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t _{D(OFF)}	_	17.5	_	115	$R_G = 2\Omega$, $I_D = 5A$
Turn-Off Fall Time	t _F	_	7.5	_		
Reverse Recovery Time	t _{RR}	_	15	_	ns	I _F = 5A, di/dt = 200A/μs
Reverse Recovery Charge	Q_{RR}	_	4	_	nC	I _F = 5A, di/dt = 200A/μs

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







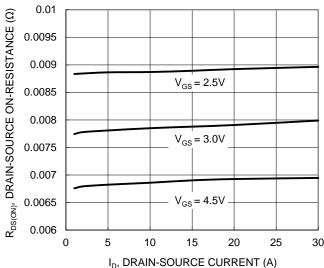


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

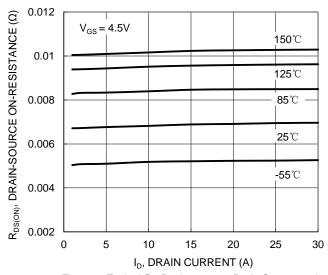
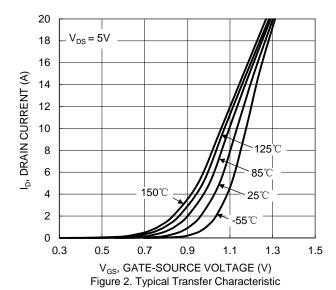


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



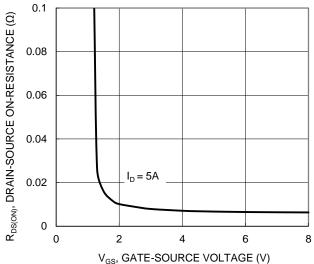


Figure 4. Typical Transfer Characteristic

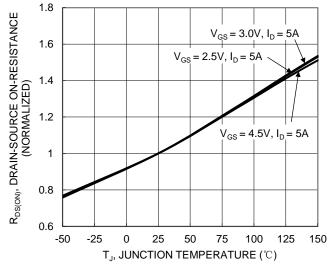


Figure 6. On-Resistance Variation with Junction Temperature





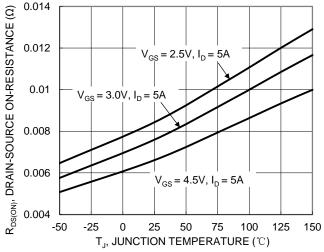


Figure 7. On-Resistance Variation with Junction Temperature

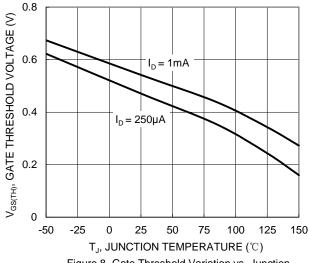


Figure 8. Gate Threshold Variation vs. Junction Temperature

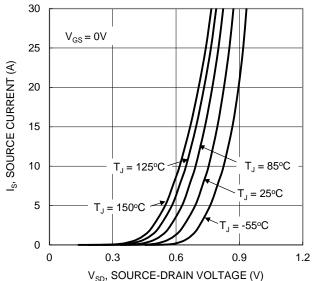
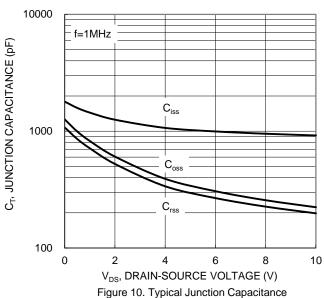


Figure 9. Diode Forward Voltage vs. Current



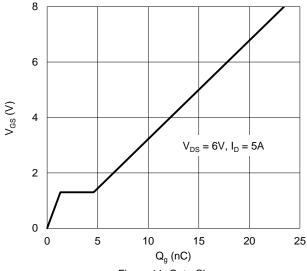


Figure 11. Gate Charge

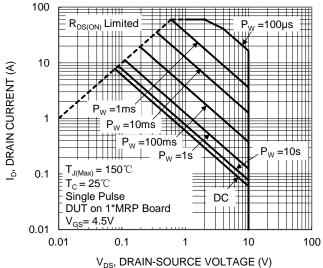


Figure 12. SOA, Safe Operation Area



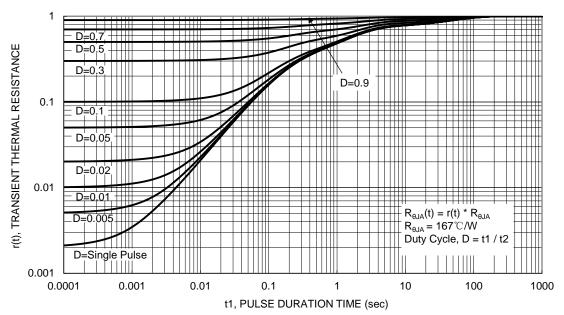


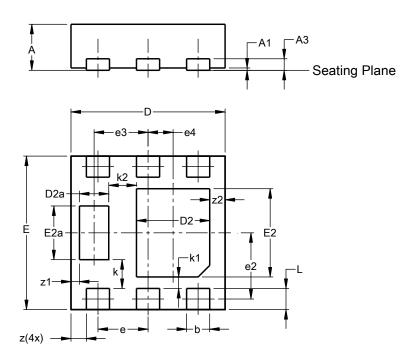
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

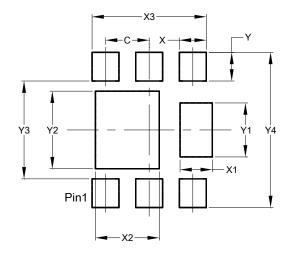


U-DFN2020-6								
(Type F)								
Dim	Min Max Typ							
Α	0.57	0.63	0.60					
A1	0.00 0.05 0.03							
А3	-	1	0.15					
b	0.25	0.35	0.30					
D	1.95	2.05	2.00					
D2	0.85	1.05	0.95					
D2a	0.33	0.43	0.38					
Е	1.95	2.05	2.00					
E2	1.05	1.25	1.15					
E2a	0.65	0.75	0.70					
е	(0.65 BS	С					
e2	C	.863 BS	SC					
e3	(0.70 BS	С					
e4	C	.325 BS	SC SC					
k	(0.37 BS	С					
k1	(0.15 BS	С					
k2	(0.36 BS	С					
L	0.225	0.325	0.275					
Z	0.20 BSC							
z 1	0.110 BSC							
z2	(0.20 BS	С					
All C	imens	ions in	mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
С	0.650
Х	0.400
X1	0.480
X2	0.950
Х3	1.700
Υ	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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